

Description

This 4-bit-inverting translator is a bidirectional voltage-level translator and can be used to build digital switching compatibility between multi voltage systems. It uses two separate configurable power supply rails that including A ports supporting operating voltages from 1.65 V to 3.6 V with tracking V_{CCA} supply, and also including B ports supporting operating voltages from 2.3 V to 5.5V with tracking V_{CCB} supply. The advantage above provides the support of both lower and higher logic signal levels while providing bidirectional translation capabilities between any of the 1.8V,2.5V,3.3V,and 5V voltage circuit points. Placing output-enable(OE) input to low level,all I/Os are forced to high-impedance state that significantly lower the quiescent current consumption. In order to ensure the high-impedance state during power up or power down, OE pin should be tied to GND via a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

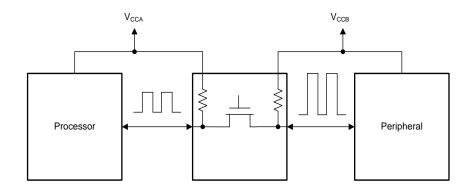
Features

- No direction-control
- Data rates24 Mbps (Push Pull)2 Mbps (Open Drain)
- 1.65V to 3.6V on A port and 2.3V to 5.5V on B port (VCCA ≤ VCCB)
- VCC isolation feature:If either VCC input is at GND,both ports are in the high-impedance state
- No power-supply sequencing required:
 either VCCA or VCCB can be ramped first
- · IOFF supports partial-power-down mode operation
- · Operating temperature range:-40°C to +85°C

Applications

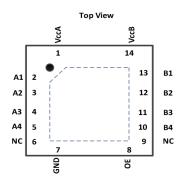
- Handset/Smartphone
- · MART
- · IPC
- · GPIO

Circuit Diagram





Pin Assignment



TXS0104ERGYR (SOP-14) Package

Device Summary, Pin and Packages (Continued)

Pin		1/0	
Name	RGY	I/O	Function
Vcca	1	-	Port Supply Voltage. 1.65V≤VccA≤3.6V and VccA≤VccB
A1	2	I/O	Input/Output A1. Referenced to V _{CCA} .
A2	3	I/O	Input/Output A2. Referenced to Vcca.
A3	4	I/O	Input/Output A3. Referenced to V _{CCA} .
A4	5	I/O	Input/Output A4. Referenced to V _{CCA} .
NC	6	-	No internal connection
GND	7	-	Ground
OE	8	1	Output Enable(Active High).Pull OE low to place all outputs in 3-state mode. Referenced to V _{CCA} .
NC	9	-	No internal connection
B4	10	I/O	Input/Output B4. Referenced to V _{CCB} .
В3	11	I/O	Input/Output B3. Referenced to V _{CCB} .
B2	12	I/O	Input/Output B2. Referenced to V _{CCB} .
B1	13	I/O	Input/Output B1. Referenced to V _{CCB} .
V _{CCB}	14	-	B Port Supply Voltage. 2.3V≤VccB≤5.5V



Oeder Information

Package	Orderable Device	Packing Qty	Body Size
QFN3.5X3.5-14L	TXS0104ERGYR	Tape and Reel,3000	3.50mm x 3.50mm

Absolute Maximum Ratings

Parameters	Min	Max	Unit	
Supply voltage, Vcca		-0.3	6.0	V
Supply voltage, Vcсв		-0.3	6.0	V
Land and the manner of	A port	-0.3	6.0	V
Input voltage range,V _I	B port	-0.3	6.0	V
Voltage range applied to any output in the high-impedance or	A port	-0.3	6.0	V
power-off state, Vo	B port	-0.3	6.0	V
Valtage range applied to any output in the high or law state. Ve	A port	-0.3	V _{CCA} +0.3	V
Voltage range applied to any output in the high or low state, Vo	B port	-0.3	V _{CCA} +0.3	V
Input clamp current, I _{IK}	V _I <0		-50	mA
Output clamp current,lok	V ₀ <0		-50	mA
Continuous output current, lo			±50	mA
Continuous current through Vcca, Vccb or GND		±100	mA	
Maximum junction temperature		150	°C	
Storage temperature range		-65	150	°C

⁽¹⁾Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

ESD Ratings

	E	SD	Value	Unit
\//ECD\	WEOD) Electricate d'a Diseile	Human-Body Model (HBM) ⁽¹⁾	±3K	V
V(ESD)	Electrostatic Discharge	Charged-Device Model (CDM)(2)	±2K	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed

⁽³⁾ The value of V_{CCA} and V_{CCB} are provided in the recommended operating conditions table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Recommended Operating Conditions

Vccı is the supply voltage associated with the input port.Vcco is the supply Voltage associated with the output port.

Parameter		Conditions		Тур	Max	Unit	
Supply voltage ⁽¹⁾	$V_{\sf CCA}$		1.65		3.6	V	
Supply voltage 🗥		V_{CCB}	2.3		5.5	V	
	A nort I/Os	V _{CCA} =1.65 V to 1.95 V V _{CCB} =2.3 V to 5.5 V	V _{CCI} -0.2		Vccı		
l limb laval	A-port I/Os	V _{CCA} =2.3 V to 3.6 V V _{CCB} =2.3 V to 5.5 V	V _{CCI} -0.4		Vccı		
High-level input voltage(V _{IH})	B-port I/Os	V _{CCA} =1.65 V to 3.6V V _{CCB} =2.3 V to 5.5 V	V _{CCI} -0.4		Vccı	V	
	OE input	V _{CCA} =1.65 V to 3.6 V V _{CCB} =2.3 V to 5.5 V	V _{CCI} ×0.8		5.5		
Low-level	A-port I/Os	V _{CCA} =1.65 V to 1.95 V V _{CCB} =2.3 V to 5.5 V	0		0.15	\/	
input voltage(VIL) ⁽²⁾	B-port I/Os	V _{CCA=} 1.65 V to 3.6 V V _{CCB} =2.3 V to 5.5 V	0		0.15	V	
OE	OE input	V _{CCA} =1.65 V to 3.6 V V _{CCB} =2.3 V to 5.5 V	0		V _{CCA} ×0.25	V	
Input transition rise or fall rate(Δt/Δv)		push-pull driving			10		
	B-port I/Os push-pull driving				10	ns/V	
οι ιαπιαιε(ΔυΔν)	C			10			
TA Operating free- air temperature	-		-40		85	°C	

⁽¹⁾ Vcca must be less than or equal to Vccb.

⁽²⁾ The maximum V_{1L} value is provided to ensure that a valid V_{0L} is maintained. The V_{0L} value is V_{1L} plus the voltage drop across the pass gate transistor.



Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted) $^{(1)}(2)(3)$

Pa	rameter	Conditions	Vcca	Vccв	Temp	Min	Тур	Max	Unit
Voha	Port A Output High Voltage	I_{OH} =-20 μ A $V_{IB} \ge V_{CCB} - 0.4V$	1.65V to 3.6V	2.3V to 5.5V	Full	V _{CCA} ×0.7			V
Vola	Port A Output Low Voltage	I _{OL} =1mA V _{IB} ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V
V _{OHB}	Port B Output High Voltage	I _{OH} =−20 μA V _{IA} ≥ V _{CCA} − 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	$V_{CCA} \times 0.7$			V
V _{OLB}	Port B Output Low Voltage	I _{OL} =1mA V _{IA} ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V
l _l	Input Leakage	OE	1.65V to 3.6V	2.3V to 5.5V	+25℃			±1	μA
	Current				Full			±1.5	P** *
		A Ports	0V	0V to 5.5V	+25℃			±0.5	
l _{off}	Partial Power	, et este		0 7 10 0.07	Full			±1	μA
ЮТ	Down Current	B Ports	0V to 3.6V	0V	+25℃			±0.5	μΛ
		Diots	0 0 10 3.00	OV	Full			±1	
loz	High-impedance State Output	A or B port	1.65V to 3.6V	2.3V to 5.5V	+25℃			±0.5	μA
IOZ	Current	OE=0V	1.030 to 3.00	2.37 to 5.57	Full			±1	μΑ
			1.65V to V _{CCB}	2.3v to 5.5V	Full			2.5	
ICCA	V _{CCA} Supply Current	V₁=V _O =open Io=0	3.6v	0V	Full			2.5	μΑ
			0v	5.5V	Full			-1	
			1.65V to V _{CCB}	2.3v to 5.5V	Full			10	
Iccb	V _{CCB} Supply Current	V _{I=} V _O =open I _O =0	3.6v	0V	Full			-1	μΑ
			0v	5.5V	Full			1	
ICCA + ICCB	Combined Supply Current	V _I =V _{CCI} or GND I _O =0	1.65V to V _{CCB}	2.3v to 5.5V	Full			13	μΑ
Iccza	V _{CCA} Supply Current	V _I =V _{CCI} or 0V I _O =0, OE=0V	1.65V to V _{CCB}	2.3v to 5.5V	Full			1	μΑ
Іссzв	V _{CCB} Supply Current	V _I =V _{CCI} or 0V I _O =0, OE=0V	2.3v to 3.6V	2.3v to 5.5V	Full			1	μΑ
Ci	Input Capacitance	OE	3.3V	3.3V	+25 ℃		2.5		PF
C _{io}	Input-to-output Internal	A Port	3.3V	3.3V	+25℃		5		PF
Οio	Capacitance	B Port	3.3V	3.3V	+25℃		5		FF

⁽¹⁾ V_{CCI} is the VCC associated with the input port.

⁽²⁾ V_{CCO} is the VCC associated with the output port

⁽³⁾ V_{CCA} must be less than or equal to V_{CCB} .



Timing Requirements

V_{CCA} =1.8 $V\pm0.15V$

		V _{CCB} =2.5V±0.2V	V _{CCB} =3.3V±0.2V	V _{CCB} =5V±0.2V	Unit
		Тур	Тур	Тур	UIIIL
D . D .	Push-pull Driving	21	22	24	Mhna
Data Rate	Open-drain Driving	2	2	2	Mbps
Pulse	Push-pull Driving (Data Inputs)	47	45	41	
Duration(tw)	Open-drain Driving (Data Inputs)	500	500	500	ns

V_{CCA} =2.5 $V\pm0.15V$

		V _{CCB} =2.5V±0.2V	V _{CCB} =3.3V±0.2V	V _{CCB} =5V±0.2V	Unit
		Тур	Тур	Тур	Offic
Data Rate	Push-pull Driving	20	22	24	Mhna
Data Rate	Open-drain Driving	2	2	2	Mbps
Pulse	Push-pull Driving (Data Inputs)	50	45	41	no
Duration(tw)	Open-drain Driving (Data Inputs)	500	500	500	ns

$V_{CCA} = 3.3V \pm 0.15V$

		V_{CCB} =3.3 V ±0.2 V	V_{CCB} =5 $V\pm0.2V$	Unit
		Тур	Тур	Unit
Data Rate	Push-pull Driving	23	24	Mbps
Data Rate	Open-drain Driving	2	2	ivibps
Pulso Duration/tw)	Push-pull Driving (Data Inputs)	43	41	no
Pulse Duration(tw)	Open-drain Driving (Data Inputs)	500	500	ns



Switching Characteristics:Vcc=1.8V±0.15V

over recommended operating free-air temperature range (unless otherwise noted)

	Parameter	Conditions		V _{ccB} =2.5V±0.2V	V _{ccB} =3.3V±0.2V	V _{ccB} =5V±0.2V	Units	
	Parameter		Conditions	Тур	Тур	Тур	Units	
t _{PHL}	Propagation Delay Time	A to B	Push-pull Driving	5.6	5	5	ns	
Y-NL	High-to-low Output	Attob	Open-drain Driving	7.5	7.9	8.3	110	
4	Propagation Delay Time	A to B	Push-pull Driving	10.0	9.5	9	ns	
tрLН	low-to-high Output	Alob	Open-drain Driving	181	170	154	115	
tрн∟	Propagation Delay Time	B to A	Push-pull Driving	7	7.1	7.2		
4112	High-to-low Output		Open-drain Driving	7.6	8.1	9.2	ns	
tрцн	Propagation Delay Time	B to A	Push-pull Driving	7.6	6.9	6	ns	
4 21	low-to-high Output		Open-drain Driving	163	145	118	110	
t _{en}	Enable Time		OE to A or B	135	159	182	ns	
t _{dis}	Disable Time		OE to A or B	170	174	181	ns	
4.	Input Rise Time	A port	Push-pull Driving	13.4	11.9	10.6	ns	
t _r A	Input Rise Time	rise time	Open-drain Driving	68	66	62	115	
t _{rB}	Input Rise Time	B port	Push-pull Driving	13	12	11.6	ns	
ив	input ruse nine	rise time	Open-drain Driving	66	65	50	115	
t _{fA}	Input Fall Time	A port fall	Push-pull Driving	5.6	4.7	4.0	ns	
ЧA	input i an Time	time	Open-drain Driving	5.0	5.1	5.2	113	
trB	Input Fall Time	B port fall	Push-pull Driving	3.0	3.0	2.9	ns	
di)	mpaci an inno	time	Open-drain Driving	6.1	5.6	4.4	.10	
t _{sk(0)}	Skew(time), Output	Cha	Channel-to-Channel Skew		0.5	0.5	ns	
Ma	ximum Data Rate		Push-pull Driving	22	23	24	Mbps	
IVIC	Jamani Data Nato		Open-drain Driving	2	2	2	ivibps	



Switching Characteristics:Vcc=2.5V±0.15V

over operating free-air temperature range (unless otherwise noted)

	Parameter	Conditions		V _{ccB} =2.5V±0.2V	V _{ccB} =3.3V±0.2V	V _{ccB} =5V±0.2V	Units	
	Parameter		Conditions	Тур	Тур	Тур	Units	
t	Propagation Delay Time	A to B	Push-pull Driving	3.5	3.5	3.2	no	
tpHL	High-to-low Output	A 10 B	Open-drain Driving	6.3	6.5	6.7	ns	
	Propagation Delay Time		Push-pull Driving	4.5	4.9	4.7		
tрцн	low-ťo-high Output	A to B	Open-drain Driving	158	152	142	ns	
tрнL	Propagation Delay Time	B to A	Push-pull Driving	3.7	3.9	4.6		
PHL	High-to-low Output	BIOA	Open-drain Driving	6	6.6	7.7	ns	
tрцн	Propagation Delay Time	B to A	Push-pull Driving	4.8	4	2.5	ns	
YLH .	low-to-high Output	DIO A	Open-drain Driving	153	138	116	113	
t _{en}	Enable Time	OE to A or B		7.7	41.8	130	ns	
t _{dis}	Disable Time		OE to A or B	175	181	182	ns	
+.	Innut Die Time	A port	Push-pull Driving	9.8	8.6	7.5	ns	
t _{rA}	Input Rise Time	Rise Time	Open-drain Driving	79	77	65	113	
	Input Rise Time	B port	Push-pull Driving	9.8	8.7	8.1	no	
trB	input Nise fillie	Rise Time	Open-drain Driving	93	68	53	ns	
t _{fA}	Input Fall Time	A port Fall	Push-pull Driving	4.6	4.1	3.6	ns	
цА	inputran rine	Time	Open-drain Driving	5.1	5.1	5.2	115	
t _{fB}	Input Fall Time	B port Fall	Push-pull Driving	4.5	4.0	4.0	ns	
LIB .	mputi an time	Time Open-drain Driving		6.9	7.4	7.8	110	
tsĸ(o)	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	0.5	ns	
Ma	ximum Data Rate		Push-pull Driving	22	24	24	Mbps	
IVIA	Amam Data Nato		Open-drain Driving	2	2	2		

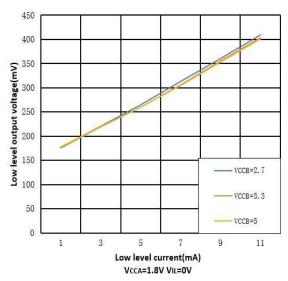


Switching Characteristics:Vcc=3.3V±0.15V

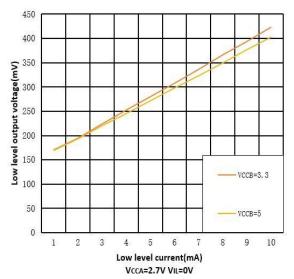
over recommended operating free-air temperature range (unless otherwise noted)

	Parameter		Conditions	V _{ccB} =3.3V±0.2V	V _{ccB} =5V±0.2V	Units
	Farameter		Conditions	TYP	TYP	Units
t _{PHL}	Propagation Delay Time	A to B	Push-pull Driving	2.1	2.2	ns
PHL	High-to-low Output	Alob	Open-drain Driving	5.9	6.1	115
	Propagation Delay Time	A	Push-pull Driving	1	3.3	
tын	High-to-low Output	A to B	Open-drain Driving	138	131	ns
tрн∟	Propagation Delay Time	B to A	Push-pull Driving	2.3	2.6	
PHL	High-to-low Output	BIOA	Open-drain Driving	5.4	6.6	ns
tецн	Propagation delay time	B to A	Push-pull Driving	1.0	1.0	ns
	low-to-high Output		Open-drain Driving	133	115	
t _{en}	Enable Time		OE to A or B	4.7	5.2	ns
t _{dis}	Disable Time		OE to A or B	174	182	ns
t _{rA}	Input Rise Time	A port	Push-pull Driving	7.4	6.6	ns
VA	input ruse rime	Rise Time	Open-drain Driving	75	67	113
tъв	Input Rise Time	B port	Push-pull Driving	7.7	7.1	ns
ırs	input ruse rime	Rise Time	Open-drain Driving	70	65	115
t _{fA}	Input Fall Time	A port Fall	Push-pull Driving	3.4	3.0	ns
ЧА	mput i all Time	Time	Open-drain Driving	5.1	5.1	113
t _{fB}	Input Fall Time	B port Fall	Push-pull Driving	3.5	3.2	ns
ЧD	mpaci all time	Time	Open-drain Driving	6.8	6.7	113
tsk(o)	Skew(time), Output	CI	nannel-to-Channel Skew	0.5	0.5	ns
М	aximum Data Rate		Push-pull Driving	24	24	Mbps
			Open-drain Driving	2	2	

Typical Characteristics



Low Level Output Voltage vs Low Level Current



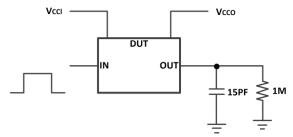
Low Level Output Voltage vs Low Level Current

Parameter Measurement Information

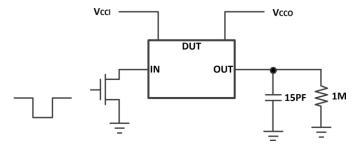
Unless otherwise noted, all input pulsed are supplied by generators having the following characteristics:

- PSRR 10MHz
- Zo=50 Ω
- dv/dt ≥1V/ns

Note: All input pulses are measured one at a time with one transition per measurement

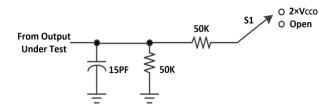


Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using a Push-Pull Driver



Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using an Open-Drain Driver

Parameter Measurement Information (Continued)

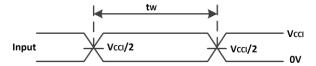


Load Circuit for Enable/Disable Time Measurement

Switch Configuration for Enable/Disable Timing

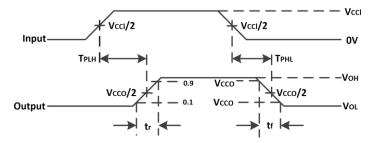
Test	S1	
t _{PZL} ⁽¹⁾ , t _{PLZ} ⁽²⁾	2×Vcco	
t pнzl ⁽¹⁾ , t pzн ⁽²⁾	Open	

- (1) t_{PZL} and t_{PZH} are the same as ten.
- (2) t_{PLZ} and t_{PHZ} are the same as tdis.

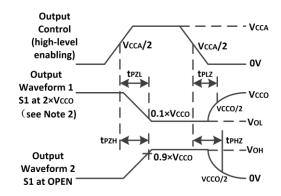


(1) All input pulses are measured one at a time, with one transition per measurement.

Voltage Waveforms Pulse Duration



Voltage Waveforms Propagation Delay Times



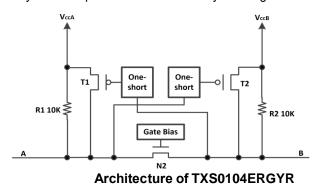
Voltage Waveforms Enable and Disable

Overview

The TXS0104ERGYR IC is a Bi-direction voltage-level translator specifically designed for translating logic voltage levels. The A port can accept I/O voltages that cover from 1.65 V to 3.6 V range; The B port can accept I/O voltages from 2.3 V to 5.5 V. The device is a pass-gate architecture with edge-rate accelerators (one-shots) to improve the overall data rate. $10-k\Omega$ pullup resistors that usually used in open-drain applications have been integrated inside IC with the advantage saving an external resistor. Not only the IC is designed for open-drain applications, but also this device can translate push-pull CMOS logic outputs.

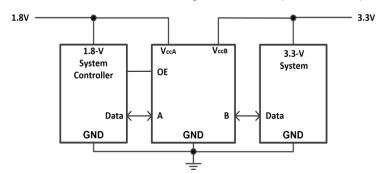
Architecture

The TXS0104ERGYR architecture (see Figure below) is a translator with Bi-direction-Sensing function that means a direction-control mechanism to control the direction of data flow from A to B or from B to A is not needed. These two bidirectional channels independently determine the direction of data flow without a direction-control signal. This auto-direction feature is realized by each I/O pin can be automatically reconfigured as either an input or an output.



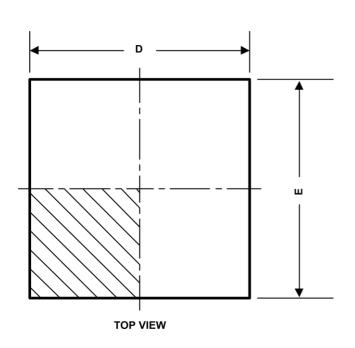
Application Information

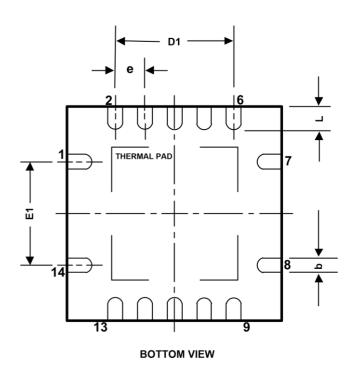
The TXS0104ERGYR device can be used to bridge the digital-switching compatibility gap between two voltage nodes to successfully interface logic threshold levels found in electronic systems. It should be used in a point-to-point topology for interfacing devices or systems operating at different interface voltages with one another. Its primary target application use is for interfacing with open-drain drivers on the data I/Os such as I2C or 1-wire, where the data is bidirectional and no control signal is available. The device can also be used in applications where a push-pull driver is connected to the data I/Os, but the WTXS0108E might be a better option for such push-pull applications.

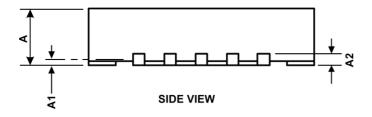


Typical Application Schematic

Package Outline Dimensions QFN3.5 X 3.5-14L







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.000	0.031	0.039
A1	0.000	0.050	0.00	0.002
A2	0.200REF		0.008REF	
b	0.180	0.300	0.007	0.012
D	3.350	3.650	0.132	0.144
D1	2.000TYP		0.079TYP	
E	3.350	3.650	0.007	0.012
E1	1.500TYP		0.059TYP	
е	0.500TYP		0.020TYP	
L	0.300	0.500	0.012	0.020



Attention

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